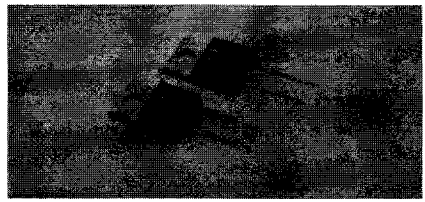
MICRO QUALITY SEMICONDUCTOR, INC

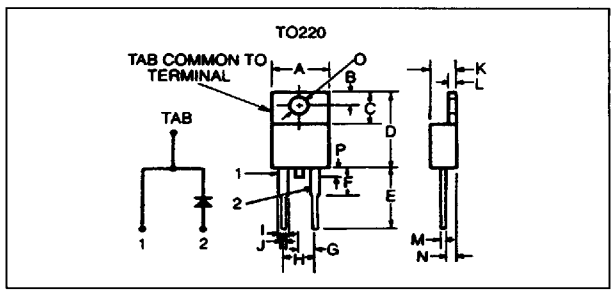
8 Amp Very Fast Recovery Rectifier

100 ns Recovery
High Voltage
High Junction Temperature
Glass Passivated



LTR.	INCHES	MILLIMETERS
A	0.415 MAX.	10,54 MAX.
B	0.108	2,74
C	0.248	6,3
D	0.605 MAX.	15,37 MAX.
E	0.552	14,02
F	0.240 MAX.	6,1 MAX.
G	0.100	2,54
H	0.200	5,08
I	0.050	1,27
J	0.032	0,81
K	0.190 MAX.	4,83 MAX.
L	0.050	1,27
M	0.022	0,56
N	0.105	2,67
O	0.143	3,63
P	0.135 MAX.	3,43 MAX.

Inch tolerances ± .005.



MAXIMUM RATINGS (At T_A = 25°C unless otherwise noted)

RATINGS	SYMBOL	TG84	TG86	TG88	TG80	UNITS
Repetitive Peak Reverse Voltage	V_{RRM}*	400	600	800	1000	V
Forward Current (Average) @ T_C = 75°C (Fig. 1)	$I_{F(AV)}$	8				A
Peak Forward Surge Current, ½ Cycle, 60 Hz, per diode	I_{FSM}	100				A
Storage Temperature	T_{STG}	−55 to +150				°C
Junction Operating Temperature	T_J	−55 to +150				°C

ELECTRICAL CHARACTERISTICS (At T_A = 25°C unless otherwise noted)

CHARACTERISTICS	SYMBOL		UNITS
Maximum Instantaneous (Fig. 2) Reverse Current at Rated V_{RRM}	I_R	T_J = 25°C: 5 T_J = 100°C: 500	µA
Maximum Instantaneous Forward Voltage @ 8 Amp (Fig. 3)	V_F	1.95	V
Reverse Recovery Time I_F = 0.5A, I_R = 1A, I_{REC} = 0.25A	t_{rr}	100	nsec
Typical Junction Capacitance, V_R = 10V (Fig. 4)	C_J	40	pF
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.0	°C/W

*V_{RRM} represents the minimum junction breakdown voltage. Lead spacing and printed wiring conductor clearances must be evaluated based on ambient conditions.